

A cross-sectional diagram of a semiconductor device. It shows two transistors on a substrate. The first transistor has a gate stack labeled 28, a channel region labeled 32, and a source/drain region labeled 26. The second transistor has a gate stack labeled 30, a channel region labeled 34, and a source/drain region labeled 26. A common source/drain region is labeled 20. Other labels include 22 and 24 pointing to different layers or regions.

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FIG. 2  
BACKGROUND ART

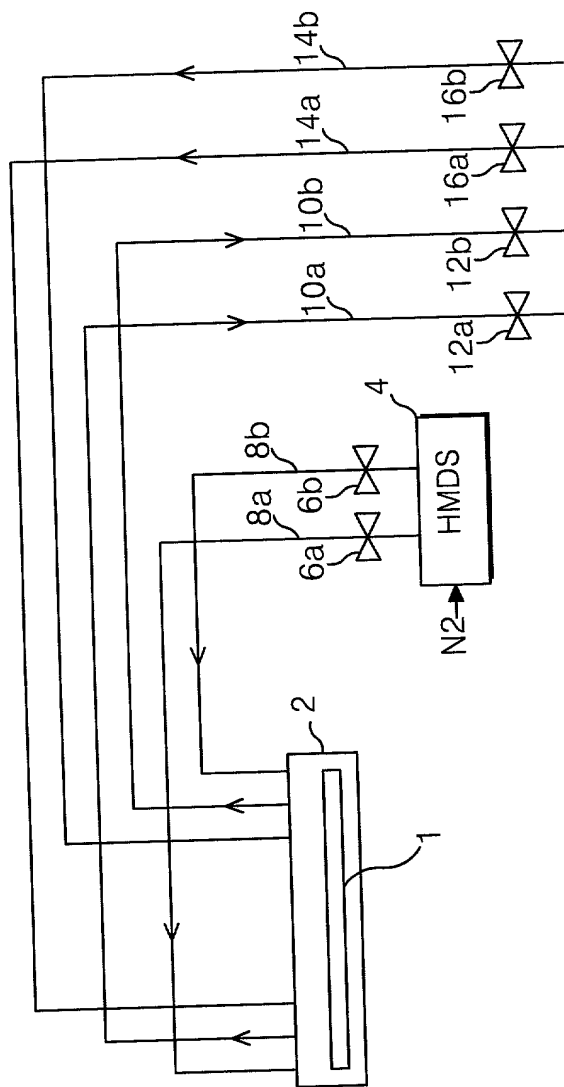


FIG. 3

